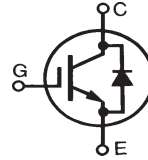


# GenX3™ 600V IGBT w/ Diode

## IXGH56N60B3D1

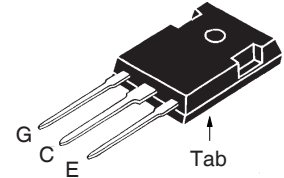
$V_{CES} = 600V$   
 $I_{C110} = 56A$   
 $V_{CE(sat)} \leq 1.80V$

Medium-Speed-Low-Vsat PT  
IGBT 5-40kHz Switching



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C110}$	$T_C = 110^\circ C$	56	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	350	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 150$ @ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	330	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g

TO-247



G = Gate      C = Collector  
 E = Emitter    Tab = Collector

### Features

- Optimized for Low Conduction and Switching losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- International Standard Package

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			300 $\mu A$ 2 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 44A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		1.49 1.47	1.80 V V

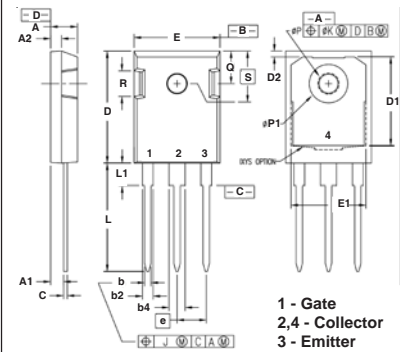
### Symbol Test Conditions

( $T_J = 25^\circ\text{C}$  Unless Otherwise Specified)

### Characteristic Values

		Min.	Typ.	Max.	
$g_{fs}$	$I_C = 44\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	36	60		S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3950		pF
$C_{oes}$			220		pF
$C_{res}$			56		pF
$Q_{g(on)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		138		nC
$Q_{ge}$			25		nC
$Q_{gc}$			47		nC
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 44\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		26		ns
$t_{ri}$			41		ns
$E_{on}$			1.30		mJ
$t_{d(off)}$			155	335	ns
$t_{fi}$			95	165	ns
$E_{off}$			1.05	2.0	mJ
$t_{d(on)}$	<b>Inductive Load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 44\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		26		ns
$t_{ri}$			37		ns
$E_{on}$			2.34		mJ
$t_{d(off)}$			220		ns
$t_{fi}$			165		ns
$E_{off}$			2.20		mJ
$R_{thJC}$				0.375	$^\circ\text{C/W}$
$R_{thCS}$		0.21			$^\circ\text{C/W}$

### TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

### Reverse Diode (FRED)

### Symbol Test Conditions

( $T_J = 25^\circ\text{C}$  Unless Otherwise Specified)

### Characteristic Values

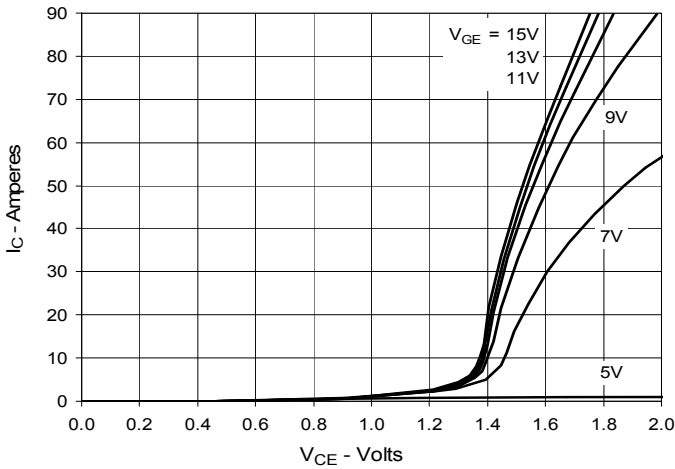
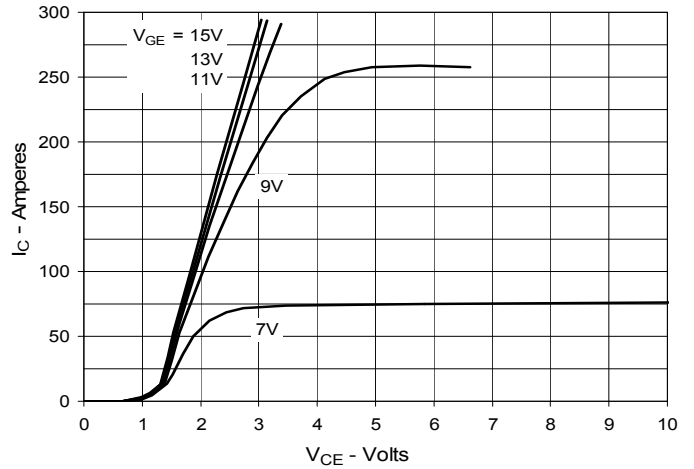
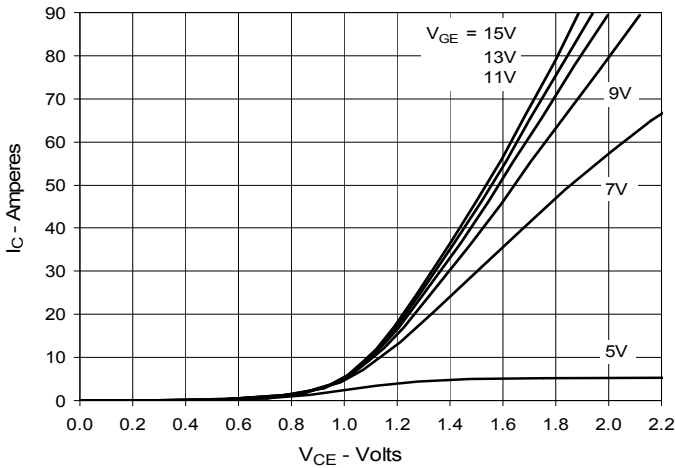
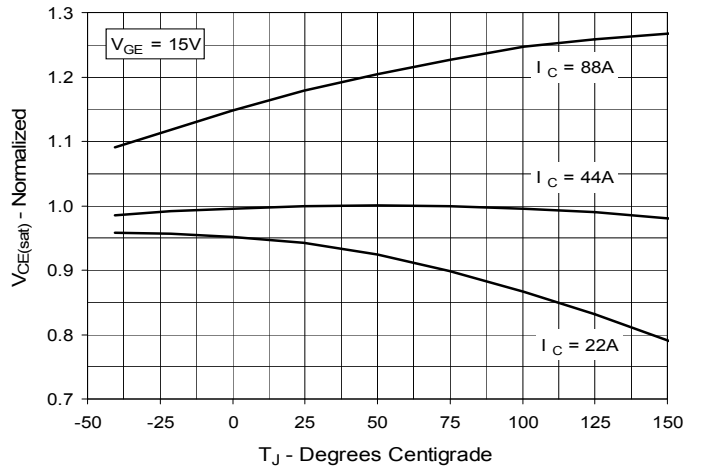
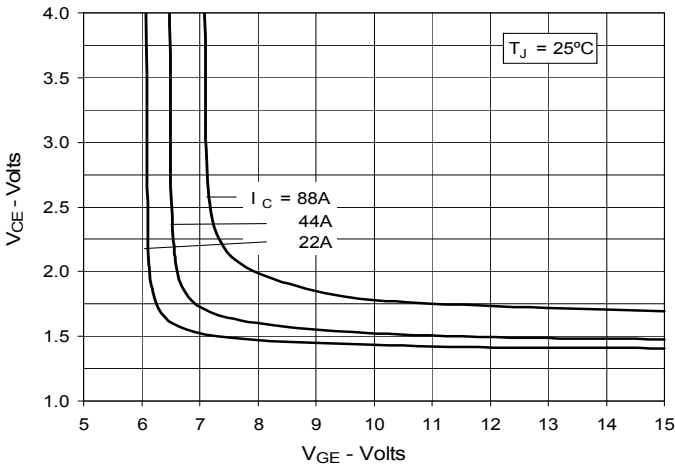
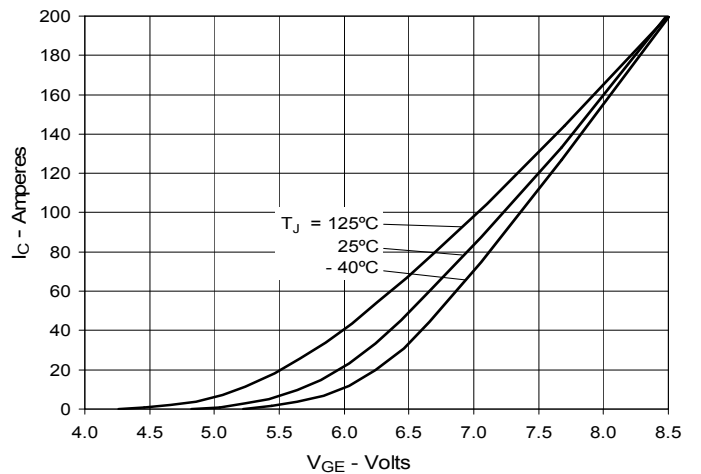
		Min.	Typ.	Max.	
$V_F$	$I_F = 30\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$			2.7	V
					V
$I_{RM}$	$I_F = 30\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, T_J = 100^\circ\text{C}$		1.6	4	A
$t_{rr}$	$V_R = 100\text{V}, T_J = 100^\circ\text{C}$		100		ns
	$I_F = 1\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 30\text{V}$		25		ns
$R_{thJC}$				0.9	$^\circ\text{C/W}$

### Notes:

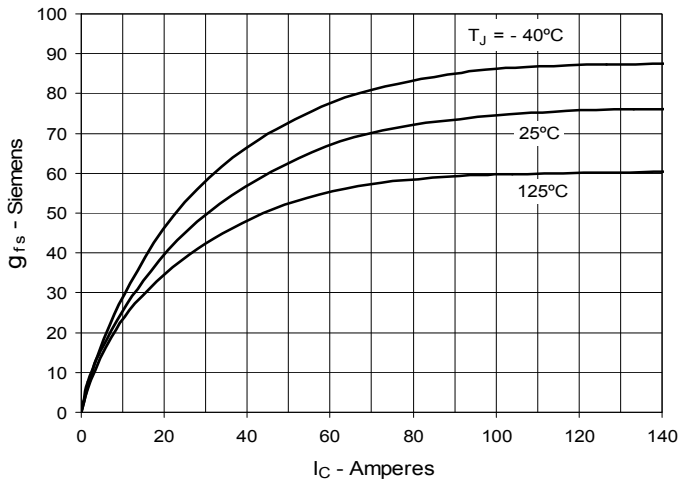
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

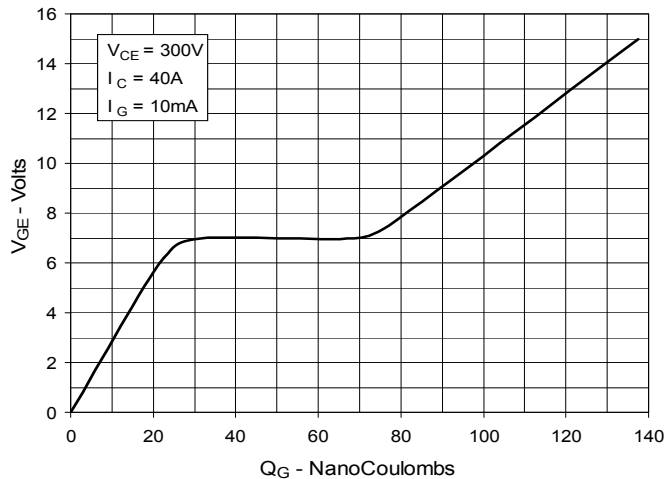
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @ 25°C**

**Fig. 2. Extended Output Characteristics @ 25°C**

**Fig. 3. Output Characteristics @ 125°C**

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


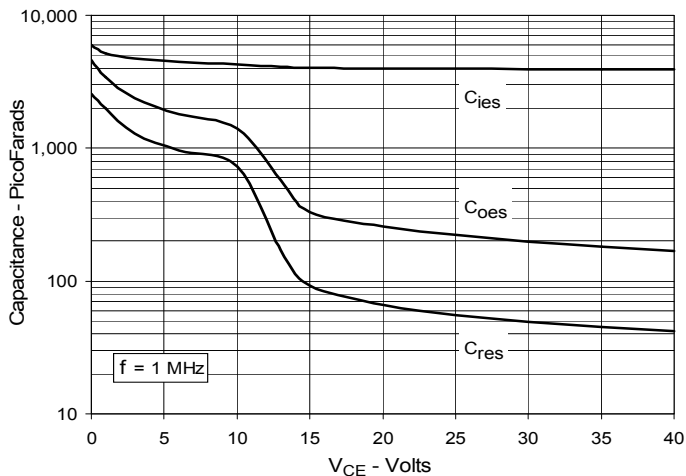
**Fig. 7. Transconductance**



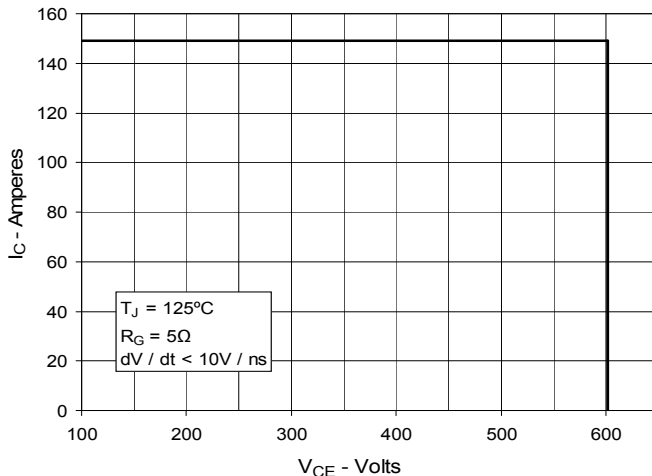
**Fig. 8. Gate Charge**



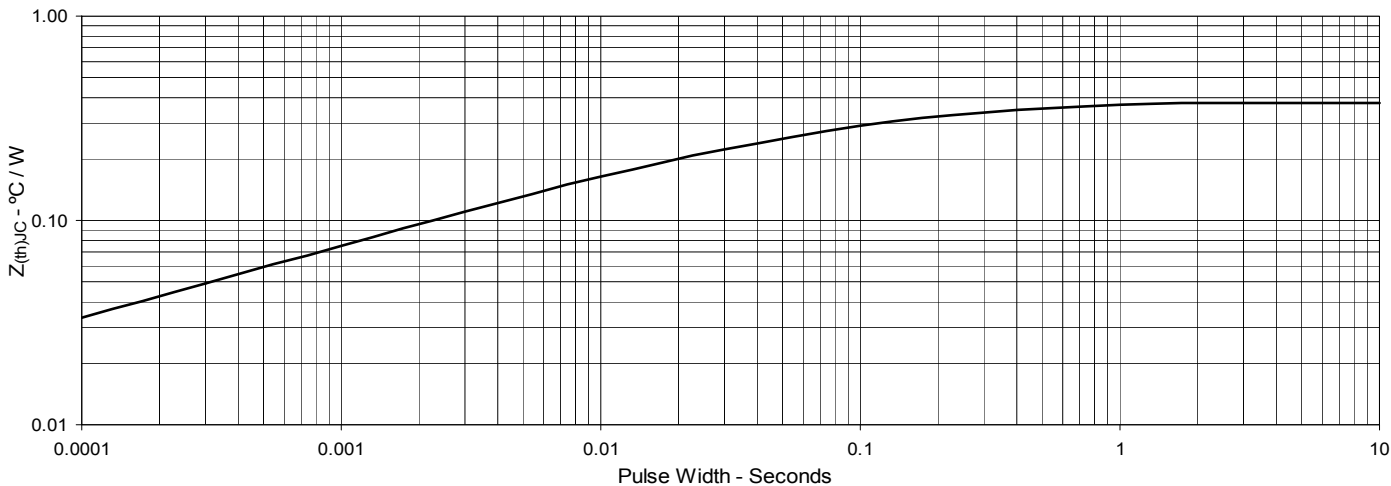
**Fig. 9. Capacitance**

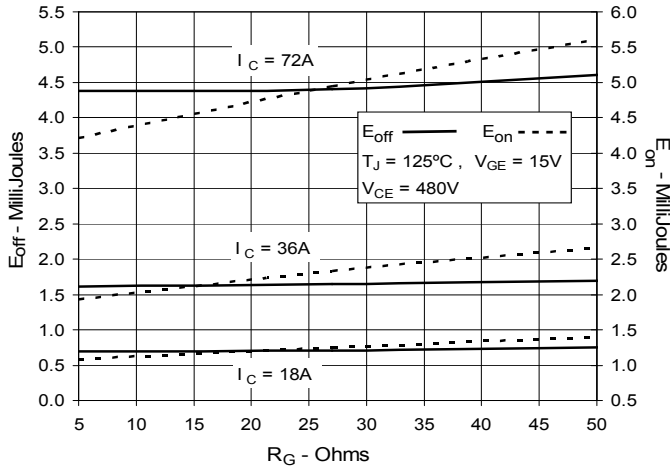
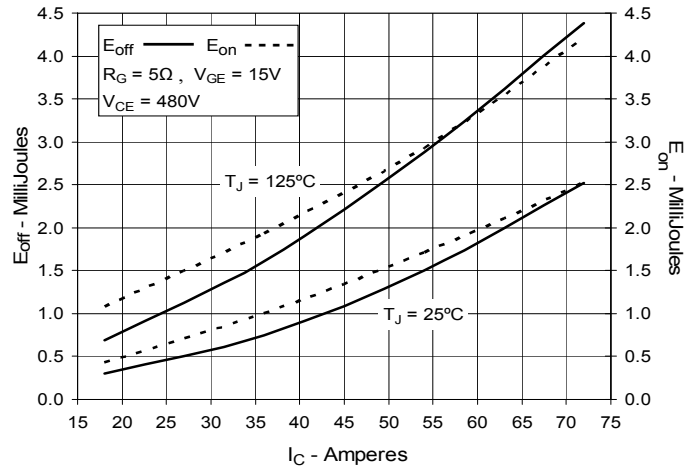
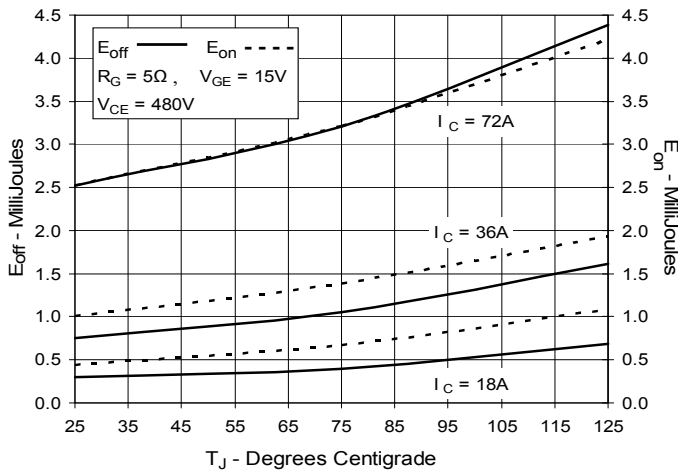
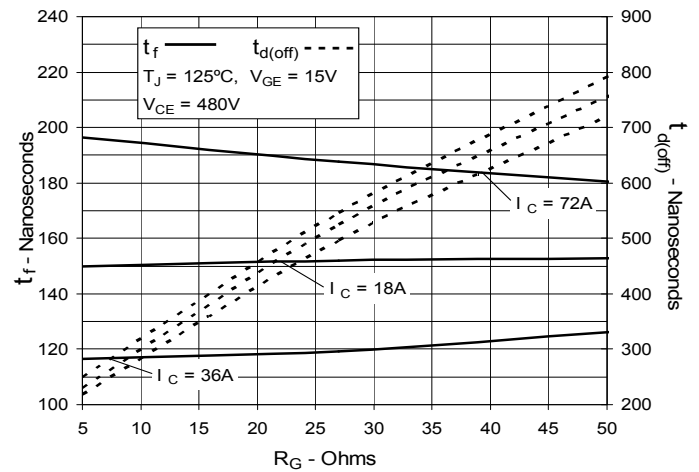
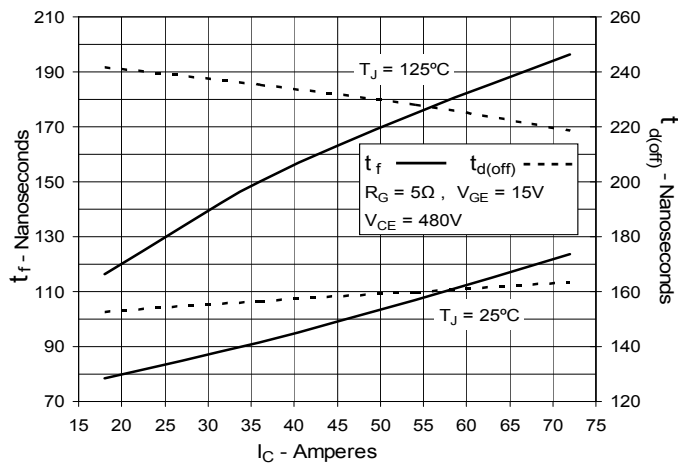
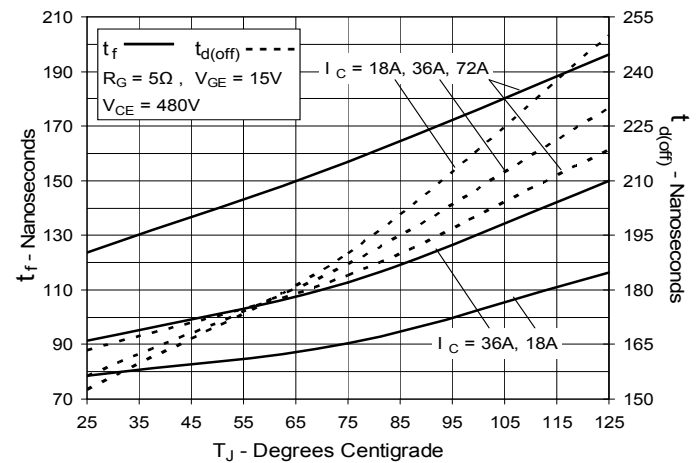


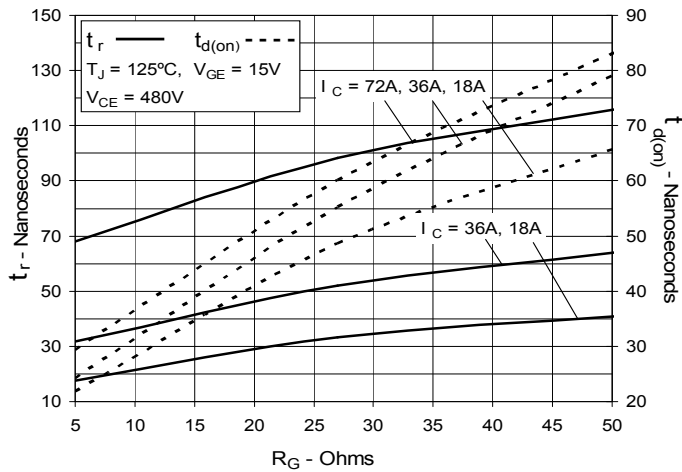
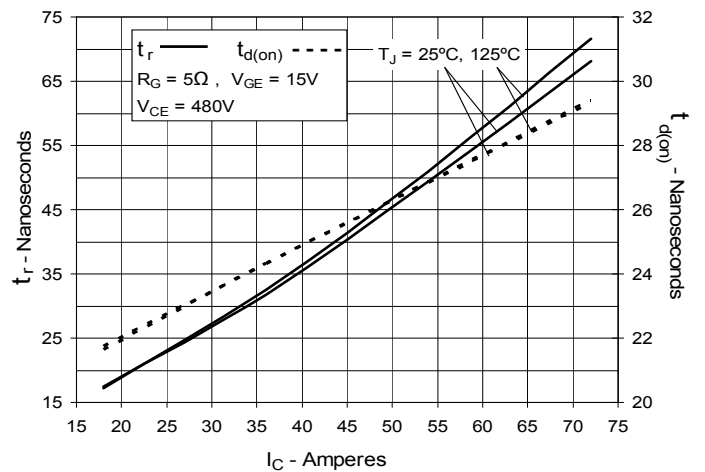
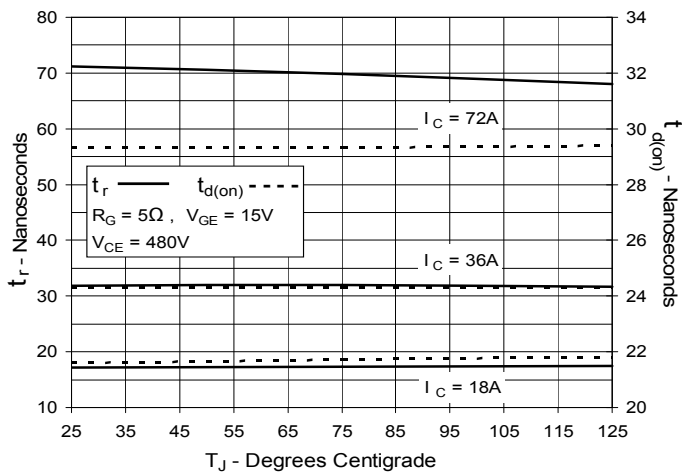
**Fig. 10. Reverse-Bias Safe Operating Area**



**Fig. 11. Maximum Transient Thermal Impedance**



**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**


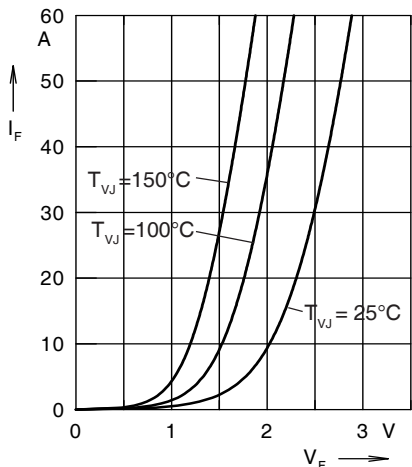


Fig. 21. Forward Current  $I_F$  Versus  $V_F$

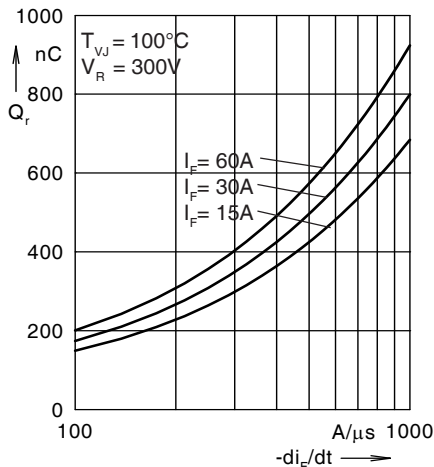


Fig. 22. Reverse Recovery Charge  $Q_r$  Versus  $-di_F/dt$

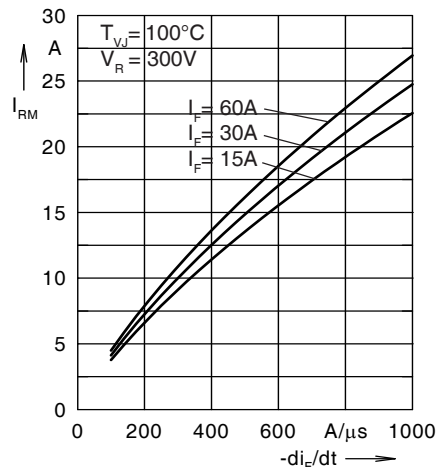


Fig. 23. Peak Reverse Current  $I_{RM}$  Versus  $-di_F/dt$

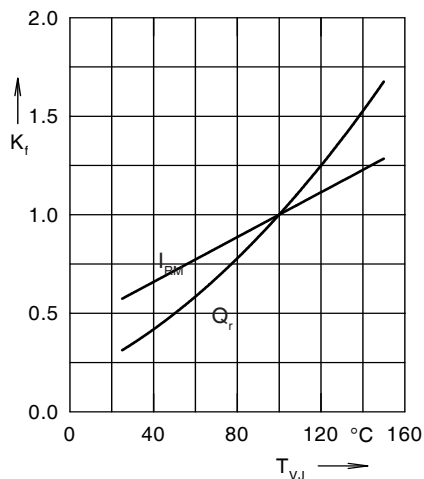


Fig. 24. Dynamic Parameters  $Q_r$ ,  $I_{RM}$  Versus  $T_{VJ}$

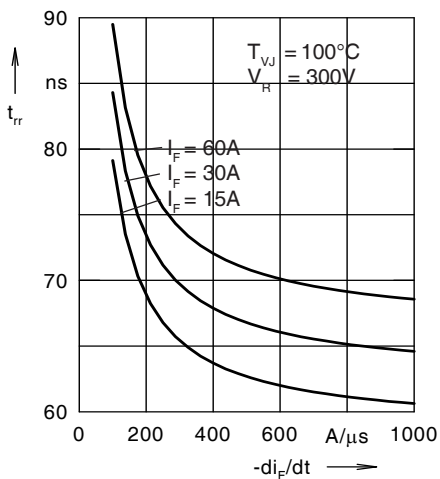


Fig. 25. Recovery Time  $t_{rr}$  Versus  $-di_F/dt$

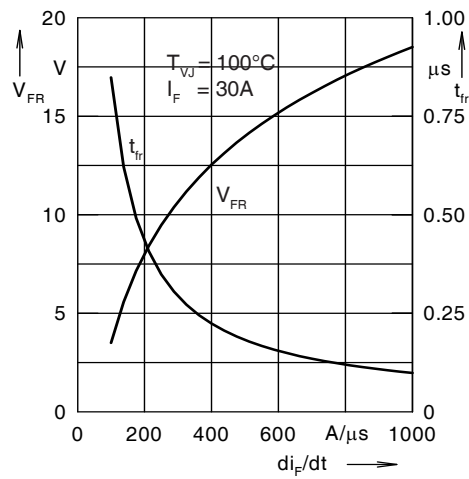


Fig. 26. Peak Forward Voltage  $V_{FR}$  and  $t_{rr}$  Versus  $di_F/dt$

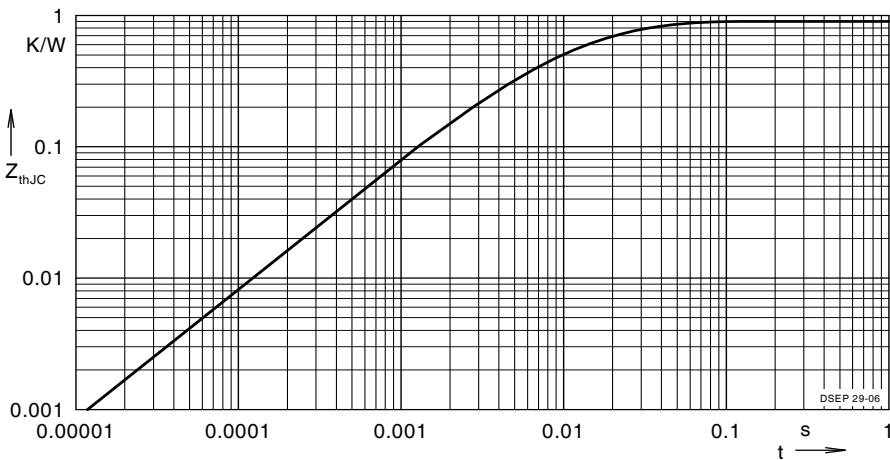


Fig. 27. Transient Thermal Resistance Junction to Case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162



---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).